No.1905B

DS441

Silicon Planar Type

Low Leak Switching Diode

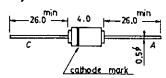
Features

- · Glass sleeve structure : DHD type
- Low leak current : $I_R = -10nA$ max. Power dissipation : P = 300mW max.
- · Interterminal capacitance: C = 6.0 pF max.

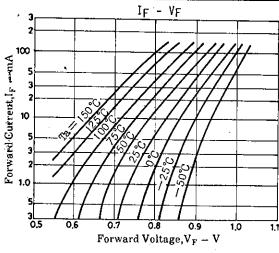
solute Maximum Ratings a			0.5	unit
Peak Reverse Voltage	$ m v_{RM}$		 35	V
Reverse Voltage	$ m v_{R}$	1 sec pulse	-30	V
Peak Forward Current	I_{FM}		300	mΑ
Average Rectified Current	I_{O}		100	mΑ
Surge Forward Current	I_{FSM}		1000	mA
Power Dissipation	P		300	mW
Junction Temperature	Tj		175	°C
Storage Temperature	Tstg		-65 to +175	°C

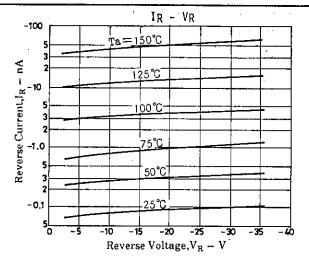
Electrical Characteristics at Ta = 25°C min typ max unit Forward Voltage $V_{\mathbf{F}}$ $I_F = 100 \text{mA}$ 1.0 1.3 $\hat{V}_R = -30V$ Reverse Current I_R -0.1-10nΑ Interterminal Capacitance $V_R = 0V, f = 1MHz$ 3.0 6.0 pF

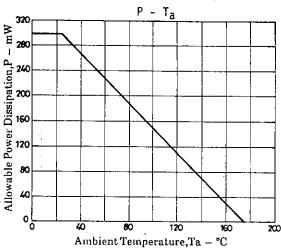
> Package Dimensions 1080 (unit: mm)



C: Cathode A: Anode







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